## FOD410, FOD4108, FOD4116, FOD4118 6-Pin DIP Zero-Cross Triac Drivers

## Features

■ 300mA on-state current
■ Zero-voltage crossing
■ High blocking voltage

- 800V (FOD4108, FOD4118)
-600V (FOD410, FOD4116)
- High trigger sensitivity
- 1.3mA (FOD4116, FOD4118)
-2mA (FOD410, FOD4108)
■ High static dv/dt $(10,000 \mathrm{~V} / \mu \mathrm{s})$
■ UL, VDE, CSA approved
■ Lead free assembly


## Applications

■ Solid-state relays

- Industrial controls
- Lighting controls
- Static power switches
- AC motor starters


## Description

The FOD410, FOD4108, FOD4116 and FOD4118 devices consist of an infrared emitting diode coupled to a hybrid triac formed with two inverse parallel SCRs which form the triac function capable of driving discrete triacs. The FOD4116 and FOD4118 utilize a high efficiency infrared emitting diode which offers an improved trigger sensitivity. These devices are housed in a standard 6-pin dual in-line (DIP) package.


Schematic

*DO NOT CONNECT
(TRIAC SUBSTRATE)

Absolute Maximum Ratings ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted)
Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

| Symbol | Parameters | Device | Value | Units |
| :---: | :---: | :---: | :---: | :---: |
| TOTAL DEVICE |  |  |  |  |
| $\mathrm{T}_{\text {STG }}$ | Storage Temperature | All | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |
| TopR | Operating Temperature | All | -55 to +100 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {SOL }}$ | Lead Solder Temperature (Wave) | All | 260 for 10 sec | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{J}}$ | Junction Temperature Range | All | 125 | ${ }^{\circ} \mathrm{C}$ |
| VISO | Isolation Test Voltage ${ }^{(1)}$ (rms AC voltage, $60 \mathrm{~Hz}, 1 \mathrm{~min}$. duration) | All | 5000 | Vac(rms) |
| $P_{D}$ | Total Device Power Dissipation @ $25^{\circ} \mathrm{C}$ Derate above $25^{\circ} \mathrm{C}$ | All | 500 | mW |
|  |  |  | 8.3 | $\mathrm{mW} /{ }^{\circ} \mathrm{C}$ |
| EMITTER |  |  |  |  |
| $I_{F}$ | Continuous Forward Current | All | 30 | mA |
| $V_{R}$ | Reverse Voltage | All | 6 | V |
| $P_{\text {D }}$ | Total Power Dissipation $25^{\circ} \mathrm{C}$ Ambient Derate above $25^{\circ} \mathrm{C}$ | All | 50 | mW |
|  |  |  | 5.4 | $\mathrm{mW} /{ }^{\circ} \mathrm{C}$ |
| DETECTOR |  |  |  |  |
| $\mathrm{V}_{\text {DRM }}$ | Off-State Output Terminal Voltage | FOD410, FOD4116 | 600 | V |
|  |  | FOD4108, FOD4118 | 800 |  |
| $\mathrm{I}_{\text {TSM }}$ | Peak Non-Repetitive Surge Current (single cycle 60 Hz sine wave) | All | 3 | A |
| $\mathrm{I}_{\text {TM }}$ | Peak On-State Current | All | 300 | mA |
| $P_{\text {D }}$ | Total Power Dissipation @ $25^{\circ} \mathrm{C}$ Ambient Derate above $25^{\circ} \mathrm{C}$ | All | 450 | mW |
|  |  |  | 6.25 | $\mathrm{mW} /{ }^{\circ} \mathrm{C}$ |

## Note:

1. Isolation voltage, $\mathrm{V}_{\text {ISO }}$, is an internal device dielectric breakdown rating. For this test, Pins 1,2 and 3 are common, and Pins 4,5 and 6 are common.

Electrical Characteristics $\left(\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}\right.$ Unless otherwise specified)
Individual Component Characteristics

| Symbol | Parameters | Test Conditions |  | Device | Min. | Typ.* | Max | Units |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| EMITTER |  |  |  |  |  |  |  |  |
| $V_{F}$ | Input Forward Voltage | $\mathrm{I}_{\mathrm{F}}=20 \mathrm{~mA}$ |  | All |  | 1.25 | 1.5 | V |
| $\mathrm{I}_{\mathrm{R}}$ | Reverse Leakage Current | $\mathrm{V}_{\mathrm{R}}=6 \mathrm{~V}$ |  | All |  | 0.0001 | 10 | $\mu \mathrm{A}$ |
| DETECTOR |  |  |  |  |  |  |  |  |
| $\mathrm{I}_{\mathrm{D} \text { (RMS) }}$ | Peak Blocking Current, Either Direction | $\begin{aligned} & \mathrm{I}_{\mathrm{F}}=0, \\ & \mathrm{~T}_{\mathrm{A}}=100^{\circ} \mathrm{C}^{(2)} \end{aligned}$ | $\mathrm{V}_{\mathrm{D}}=800 \mathrm{~V}$ | $\begin{aligned} & \hline \text { FOD4108, } \\ & \text { FOD4118 } \end{aligned}$ |  | 3 | 100 | $\mu \mathrm{A}$ |
|  |  |  | $\mathrm{V}_{\mathrm{D}}=600 \mathrm{~V}$ | $\begin{aligned} & \text { FOD410, } \\ & \text { FOD4116 } \end{aligned}$ |  |  |  |  |
| $\mathrm{I}_{\mathrm{R} \text { (RMS) }}$ | Reverse Current | $\mathrm{T}_{\mathrm{A}}=100^{\circ} \mathrm{C}$ | $\mathrm{V}_{\mathrm{D}}=800 \mathrm{~V}$ | $\begin{aligned} & \text { FOD4108, } \\ & \text { FOD4118 } \end{aligned}$ |  | 3 | 100 | $\mu \mathrm{A}$ |
|  |  |  | $\mathrm{V}_{\mathrm{D}}=600 \mathrm{~V}$ | $\begin{aligned} & \hline \text { FOD410, } \\ & \text { FOD4116 } \end{aligned}$ |  |  |  |  |
| dv/dt | Critical Rate of Rise of Off-State Voltage | $\mathrm{I}_{\mathrm{F}}=0^{(4)}$ (Fig. 11) |  |  | 10,000 |  |  | V/us |

Transfer Characteristics

${ }^{*}$ Typical values at $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$

Electrical Characteristics $\left(\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}\right.$ Unless otherwise specified) (Continued)

## Zero Crossing Characteristics

| Symbol | DC Characteristics | Test Conditions | Min. | Typ.* | Max. | Units |
| :---: | :--- | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {INH }}$ | Inhibit Voltage (MT1-MT2 voltage <br> above which device will not trigger) | $\mathrm{I}_{\mathrm{F}}=$ Rated $\mathrm{I}_{\mathrm{FT}}$ |  | 8 | 25 | V |
| $\mathrm{I}_{\mathrm{DRM2}}$ | Leakage in Inhibited State | $I_{\mathrm{F}}=$ Rated $\mathrm{I}_{\mathrm{FT}}$, <br> Rated $\mathrm{V}_{\mathrm{DRM}}$, off state |  | 20 | 200 | $\mu \mathrm{~A}$ |

Isolation Characteristics

| Symbol | Characteristics | Test Conditions | Min. | Typ.* | Max. | Units |
| :---: | :--- | :--- | :--- | :--- | :--- | :---: |
| $\mathrm{V}_{\text {ISO }}$ | Input-Output Isolation <br> Voltage | $\mathrm{f}=60 \mathrm{~Hz}, \mathrm{t}=1$ min. $^{(5)}$ | 5000 |  |  | Vac(rms) |

*Typical values at $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$

## Notes:

2. Test voltage must be applied within dv/dt rating.
3. All devices are guaranteed to trigger at an $\mathrm{I}_{\mathrm{F}}$ value less than or equal to max $\mathrm{I}_{\mathrm{FT}}$. Therefore, recommended operating $I_{F}$ lies between max $I_{F T}(2 \mathrm{~mA}$ for FOD410 and FOD4108 and 1.3 mA for FOD4116 and FOD4118 and the absolute $\max \mathrm{I}_{\mathrm{F}}(60 \mathrm{~mA})$.
4. This is static $d v / d t$. See Figure 11 for test circuit. Commutating $d v / d t$ is a function of the load-driving thyristor(s) only.
5. Isolation voltage, $\mathrm{V}_{\text {ISO }}$, is an internal device dielectric breakdown rating. For this test, Pins 1, 2 and 3 are common, and Pins 4,5 and 6 are common.

## Typical Application

Typical circuit for use when hot line switching is required. In this circuit the "hot" side of the line is switched and the load connected to the cold or neutral side. The load may be connected to either the neutral or hot line.
$R_{\text {in }}$ is calculated so that $I_{F}$ is equal to the rated $I_{F T}$ of the part, 2 mA for FOD410 and FOD4108, 1.3mA for FOD4116 and FOD4118. The $39 \Omega$ resistor and $0.01 \mu \mathrm{~F}$ capacitor are for snubbing of the triac and may or may not be necessary depending upon the particular triac and load use.


* For highly inductive loads (power factor < 0.5), change this value to 360 ohms.

Figure 1. Hot-Line Switching Application Circuit

## Typical Performance Curves

Figure 2. Forward Voltage ( $\mathrm{V}_{\mathrm{F}}$ ) vs. Forward Current ( $\mathrm{I}_{\mathrm{F}}$ )


Figure 4. Peak LED Current vs. Duty Factor, Tau


Figure 6. Pulse Trigger Current


Figure 3. Normalized LED Trigger Current ( $\mathrm{I}_{\mathrm{FT}}$ ) vs. Ambient Temperature ( $\mathrm{T}_{\mathrm{A}}$ )


Figure 5. Trigger Delay Time


Figure 7. On-State Voltage ( $\mathrm{V}_{\mathrm{TM}}$ ) vs. On-State Current ( $\mathrm{I}_{\mathrm{TM}}$ )


## Typical Performance Curves (Continued)

Figure 8. Normalized Holding Current ( $\mathrm{I}_{\mathrm{H}}$ )


Figure 10. Normalized Inhibit Voltage ( $\mathrm{V}_{\mathrm{INH}}$ )


Figure 9. Off-State Current ( $\mathrm{I}_{\mathrm{BD}}$ ) vs. Ambient Temperature ( $\mathrm{T}_{\mathrm{A}}$ )


Figure 11. Normalized Leakage in Inhibit State (IDRM) vs. Ambient Temperature ( $\mathrm{T}_{\mathrm{A}}$ )




Figure 12. Inverse-Parallel SCR Driver Circuit

Suggested method of firing two, back-to-back SCR's with a Fairchild triac driver. Diodes can be 1N4001; resistors, R1 and R2, are optional $330 \Omega$.

Note: This optoisolator should not be used to drive a load directly. It is intended to be a discrete triac driver device only.

## Package Dimensions

Through Hole

0.4" Lead Spacing


Surface Mount


Recommended Pad Layout for Surface Mount Leadforms


## Note:

All dimensions are in inches (millimeters)

## Ordering Information

| Option | Order Entry Identifier <br> (example) | Description |
| :---: | :---: | :--- |
| None | FOD410 | Standard Through Hole Device |
| S | FOD410S | Surface Mount Lead Bend |
| SD | FOD410SD | Surface Mount; Tape and reel |
| T | FOD410T | 0.4" Lead Spacing |
| V | FOD410V | IEC60747-5-2 certification |
| TV | FOD410TV | IEC60747-5-2 certification, 0.4" Lead Spacing |
| SV | FOD410SV | IEC60747-5-2 certification, Surface Mount |
| SDV | FOD410SDV | IEC60747-5-2 certification, Surface Mount, Tape \& Reel |

## Carrier Tape Specifications



## Note:

All dimensions are in inches (millimeters).

## Reflow Profile



- Peak reflow temperature: 260C (package surface temperature)
- Time of temperature higher than 183C for 160 seconds or less
- One time soldering reflow is recommended


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